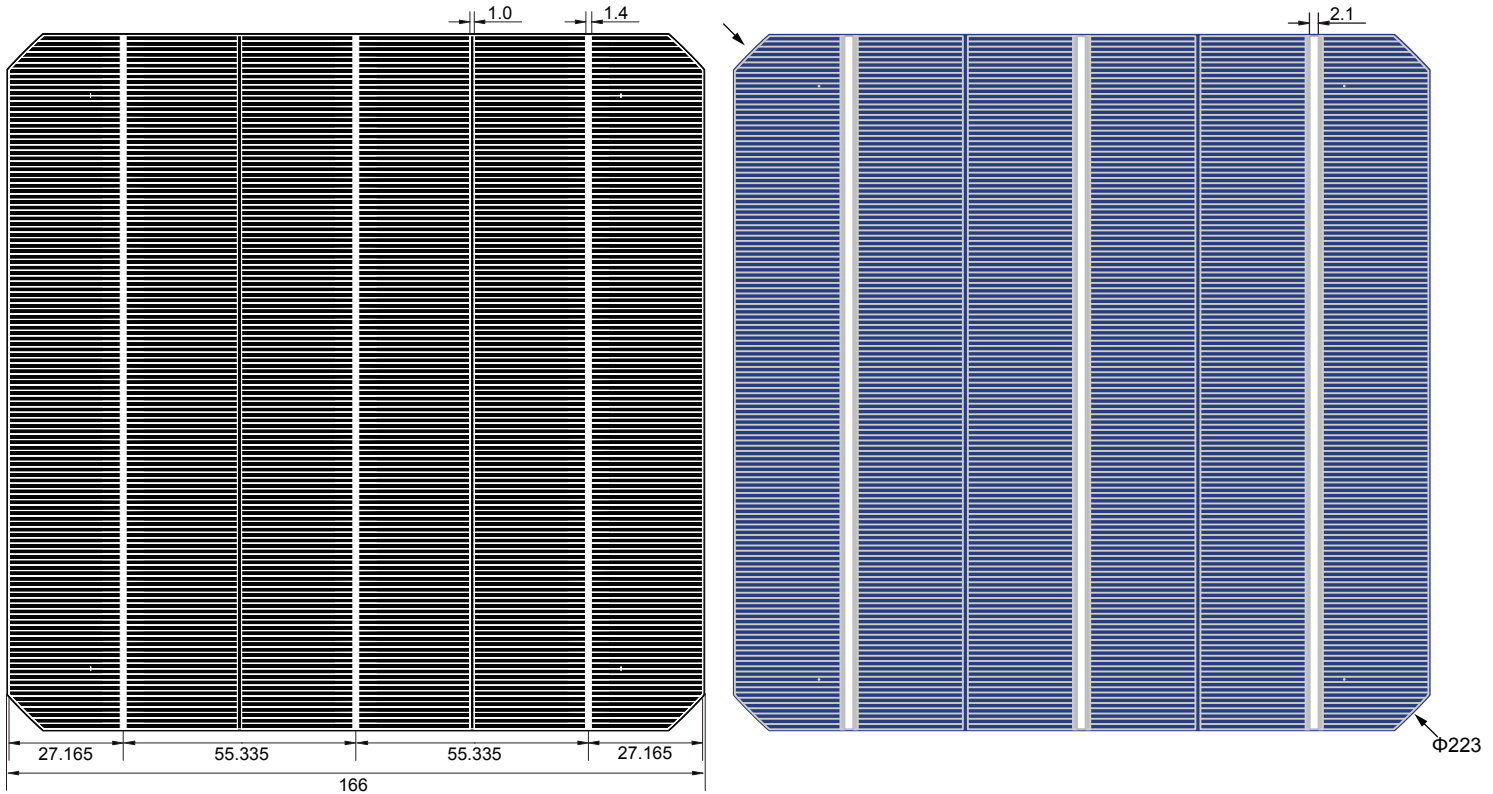




Mono-crystalline Silicon 6" PERC Bifacial Solar Cell

B7F3B



Physical Characteristics

Cell type	Mono-crystalline Silicon PERC Bifacial Solar Cell
Dimension	166 mm X 166 mm \pm 0.25 mm 223 mm \pm 0.25 mm (Diagonal length)
Cell Thickness	170 μ m \pm 30 μ m
Front side (–)	Silicon nitride anti-reflective coating and 128 fingers Three 1.4 \pm 0.1 mm wide bus bars with distance 55.335 mm
Back side (+)	Silicon nitride anti-reflective coating and 133 fingers Three 2.1 \pm 0.1 mm continuous soldering pads

B7F3B

General Characteristics

Eff(%)	Pmpp(Pmax)	Voc	Isc	Vmpp(Vmp)	Impp(Imp)
21.9	6.004	0.672	11.801	0.541	11.092
22.0	6.031	0.673	11.803	0.543	11.101
22.1	6.059	0.674	11.818	0.545	11.127
22.2	6.086	0.675	11.831	0.546	11.141
22.3	6.114	0.677	11.842	0.548	11.165
22.4	6.141	0.678	11.854	0.549	11.180
22.5	6.168	0.680	11.861	0.551	11.192
22.6	6.196	0.681	11.867	0.553	11.198
22.7	6.223	0.682	11.871	0.555	11.213
22.8	6.251	0.683	11.877	0.557	11.229
22.9	6.278	0.684	11.879	0.559	11.240
23.0	6.305	0.685	11.889	0.561	11.249

- Under standard test condition : 1000W / m² , AM 1.5 , 25°C ● Illustration : 22.7% → actual range 22.70%~22.79%
- Specification and data are for reference only and may change without prior notice.

Temperature Coefficient

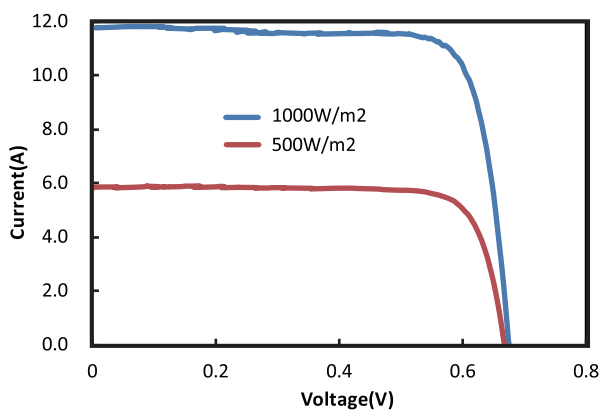
Voc	Isc	FF	Power
-0.2662%/K	0.0624%/K	-0.1071%/K	-0.3086%/K

Solderability

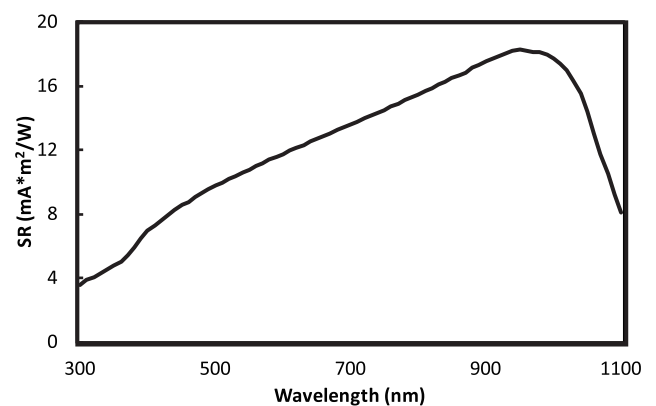
Peeling Strength ≥ 1.25 N/mm

Soldering result may vary due to different ribbons, flux, and soldering parameters.

Typical I-V Curve



Spectral Response



Electrical Properties

Parameter	Grade A
Cell efficiency / P _{mp}	Measured cell efficiency (or P _{mp}) according to above mentioned bin criteria (AM 1.5, 1000 W/m ² , 25 °C)
Shunt resistivity	> 30 Ohm
Reverse dark current	I _{rev 2} < 1.5A at -12V and 25°C